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- Trimmed Offset Voltage: TLC27L7 . . . 500 μV Max at 25°C, V_{DD} = 5 V
- Input Offset Voltage Drift . . . Typically 0.1 μV/Month, Including the First 30 Days
- Wide Range of Supply Voltages Over Specified Temperature Range:

0°C to 70°C . . . 3 V to 16 V -40°C to 85°C . . . 4 V to 16 V -55°C to 125°C . . . 4 V to 16 V

- Single-Supply Operation
- Common-Mode Input Voltage Range Extends Below the Negative Rail (C-Suffix, I-Suffix Types)
- Ultra-Low Power . . . Typically 95 μW at 25°C, V_{DD} = 5 V
- Output Voltage Range Includes Negative Rail
- High Input Impedance . . . $10^{12} \Omega$ Typ
- ESD-Protection Circuitry
- Small-Outline Package Option Also Available in Tape and Reel
- Designed-In Latch-Up immunity

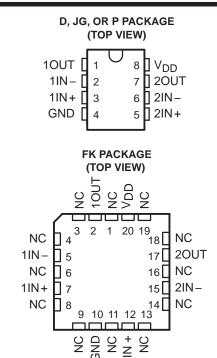
description

The TLC27L2 and TLC27L7 dual operational amplifiers combine a wide range of input offset voltage grades with low offset voltage drift, high input impedance, extremely low power, and high gain.

AVAILABLE OPTIONS

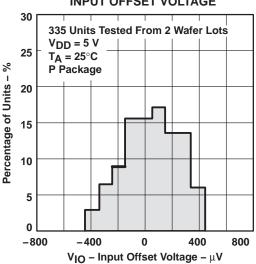
			PACKA	GE	
TA	V _{IO} max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)
0°C to 70°C	500 μV 2 mV 5 mV 10 mV	TLC27L7CD TLC27L2BCD TLC27L2ACD TLC27L2CD	I	ı	TLC27L7CP TLC27L2BCP TLC27L2ACP TLC27L2CP
-40°C to 85°C	500 μV 2 mV 5 mV 10 mV	TLC27L7ID TLC27L2BID TLC27L2AID TLC27L2ID	I	I	TLC27L7IP TLC27L2BIP TLC27L2AIP TLC27L2IP
-55°C to 125°C	500 μV 10 mV	TLC27L7MD TLC27L2MD TLC27L2MDRG4	TLC27L7MFK TLC27L2MFK	TLC27L7MJG TLC27L2MJG	TLC27L7MP TLC27L2MP

The D package is available taped and reeled. Add R suffix to the device type (e.g., TLC27L7CDR).



NC - No internal connection

DISTRIBUTION OF TLC27L7 INPUT OFFSET VOLTAGE





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description (continued)

These devices use Texas Instruments silicon-gate LinCMOS™ technology, which provides offset voltage stability far exceeding the stability available with conventional metal-gate processes.

The extremely high input impedance, low bias currents, and low power consumption make these cost-effective devices ideal for high gain, low frequency, low power applications. Four offset voltage grades are available (C-suffix and I-suffix types), ranging from the low-cost TLC27L2 (10 mV) to the high-precision TLC27L7 (500 μ V). These advantages, in combination with good common-mode rejection and supply voltage rejection, make these devices a good choice for new state-of-the-art designs as well as for upgrading existing designs.

In general, many features associated with bipolar technology are available in LinCMOS™ operational amplifiers, without the power penalties of bipolar technology. General applications such as transducer interfacing, analog calculations, amplifier blocks, active filters, and signal buffering are easily designed with the TLC27L2 and TLC27L7. The devices also exhibit low voltage single-supply operation and ultra-low power consumption, making them ideally suited for remote and inaccessible battery-powered applications. The common-mode input voltage range includes the negative rail.

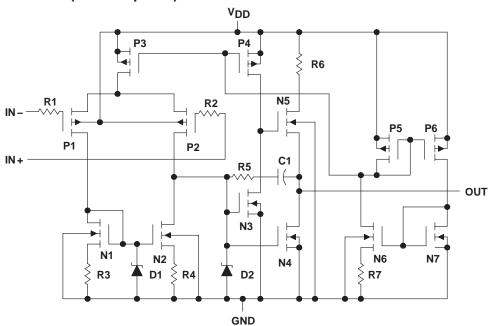
A wide range of packaging options is available, including small-outline and chip-carrier versions for high-density system applications.

The device inputs and outputs are designed to withstand – 100-mA surge currents without sustaining latch-up.

The TLC27L2 and TLC27L7 incorporate internal ESD-protection circuits that prevent functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2; however, care should be exercised in handling these devices as exposure to ESD may result in the degradation of the device parametric performance.

The C-Suffix devices are characterized for operation from 0° C to 70° C. The I-suffix devices are characterized for operation from -40° C to 85° C. The M-suffix devices are characterized for operation over the full military temperature range of -55° C to 125° C.

equivalent schematic (each amplifier)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	
Differential input voltage (see Note 2)	±V _{DD}
Input voltage range, V _I (any input)	–0.3 V to V _{DD}
Input current, I ₁	±5 mA
Output current, I _O (each output)	±30 mA
Total current into V _{DD}	45 mA
Total current out of GND	
Duration of short-circuit current at (or below) 25°C (see Note 3)	Unlimited
Continuous total dissipation	See Dissipation Rating Table
Continuous total dissipation	
	0°C to 70°C
Operating free-air temperature, T _A : C suffix	0°C to 70°C40°C to 85°C
Operating free-air temperature, T _A : C suffix	
Operating free-air temperature, T _A : C suffix	
Operating free-air temperature, T _A : C suffix	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to network ground.
 - 2. Differential voltages are at IN+ with respect to IN-.
 - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded (see application section).

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW	_
FK	1375 mW	11 mW/°C	880 mW	715 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	546 mW	210 mW
Р	1000 mW	8 mW/°C	640 mW	520 mW	_

recommended operating conditions

		C SU	FFIX	I SUF	FIX	M SU	FFIX	LINUT
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V _{DD}		3	16	4	16	4	16	V
O	V _{DD} = 5 V	-0.2	3.5	-0.2	3.5	0	3.5	.,
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	-0.2	8.5	-0.2	8.5	0	8.5	V
Operating free-air temperature, T _A		0	70	-40	85	-55	125	°C



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electrical characteristics at specified free-air temperature, $V_{\mbox{\scriptsize DD}}$ = 5 V (unless otherwise noted)

	PARAMETER		TEST CONE	DITIONS	T _A †	TL(C27L2C C27L2A C27L2B C27L7C	C C	UNIT
						MIN	TYP	MAX	
		TLC27L2C	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		1.1	10	
		TLGZ/LZG	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			12	mV
		TLC27L2AC	$V_0 = 1.4 V,$	$V_{IC} = 0$,	25°C		0.9	5	IIIV
VIO	Input offset voltage	TLG27L2AC	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			6.5	
VIO	iliput oliset voltage	TLC27L2BC	$V_{O} = 1.4 V,$	$V_{IC} = 0$,	25°C		204	2000	
		TEGZTEZBC	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			3000	μV
		TLC27L7C	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		170	500	μν
		TLC27L7C	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			1500	
ανιο	Average temperature coeff offset voltage	icient of input			25°C to 70°C		1.1		μV/°C
					25°C		0.1	60	
IIO	Input offset current (see No	ote 4)	$V_0 = 2.5 \text{ V},$	$V_{IC} = 2.5 V$	70°C		7	300	pA
					25°C		0.6	60	_
lΒ	Input bias current (see Not	e 4)	$V_0 = 2.5 \text{ V},$	$V_{IC} = 2.5 V$	70°C		50	600	pA
						-0.2	-0.3		
	Common-mode input volta	ge range			25°C	to 4	to 4.2		V
VICR	(see Note 5)	gerange			Full range	-0.2 to 3.5			V
					25°C	3.2	4.1		
Vон	High-level output voltage		$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	0°C	3	4.1		V
					70°C	3	4.2		
					25°C		0	50	
VOL	Low-level output voltage		$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
					70°C		0	50	
					25°C	50	700		
AVD	Large-signal differential vo amplification	ltage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 1 M\Omega$	0°C	50	700		V/mV
	amplification				70°C	50	380		
					25°C	65	94		
CMRR	Common-mode rejection ra	atio	V _{IC} = V _{ICR} min		0°C	60	95		dB
					70°C	60	95		
					25°C	70	97		
ksvr	Supply-voltage rejection ra (ΔV _{DD} /ΔV _{IO})	tio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V _O = 1.4 V	0°C	60	97		dB
	(¬ , DD, ¬ , IO)				70°C	60	98		
				.,	25°C		20	34	
IDD	Supply current (two amplifi	ers)	V _O = 2.5 V, No load	$V_{IC} = 2.5 V,$	0°C		24	42	μΑ
			110 1000		70°C		16	28	

[†] Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



^{5.} This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, $V_{\mbox{DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †	TL:	C27L2C C27L2A C27L2B C27L7C	C C	UNIT
						MIN	TYP	MAX	
		TLC27L2C	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		1.1	10	
		11.0271.20	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			12	mV
		TLC27L2AC	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		0.9	5	IIIV
\/. o	Input offset voltage	TLC27L2AC	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			6.5	
VIO	input onset voltage	TLC27L2BC	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		235	2000	
		TLC27L2BC	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			3000	μV
		TLC27L7C	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		190	800	
		TLC27L7C	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			1900	
ανιο	Average temperature of	pefficient of input			25°C to		1		μV/°C
	offset voltage				70°C				•
IIO	Input offset current (see	Note 4)	V _O = 5 V,	V _{IC} = 5 V	25°C		0.1	60	рA
		,	,	10 -	70°C		8	300	
I _{IB}	Input bias current (see	Note 4)	V _O = 5 V,	V _{IC} = 5 V	25°C		0.7	60	рA
		,	,	10 -	70°C		50	600	
					0500	-0.2	-0.3		V
	Common-mode input vo	oltane ranne			25°C	to 9	to 9.2		V
VICR	(see Note 5)	sitage range			Full range	-0.2			V
					Full range	to 8.5			V
					25°C	8	8.9		
VOH	High-level output voltage	16	V _{ID} = 100 mV,	$R_{I} = 1 M\Omega$	0°C	7.8	8.9		V
0		•		_	70°C	7.8	8.9		
					25°C		0	50	
VOL	Low-level output voltag	e	$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	0°C		0	50	mV
02				OL.	70°C		0	50	
					25°C	50	860		
A _{VD}	Large-signal differential	voltage	$V_{O} = 1 \text{ V to 6 V},$	$R_{\parallel} = 1 M\Omega$	0°C	50	1025		V/mV
'	amplification		•	_	70°C	50	660		
					25°C	65	97		
CMRR	Common-mode rejection	n ratio	V _{IC} = V _{ICR} min		0°C	60	97		dB
	,				70°C	60	97		
					25°C	70	97		
ksvr	Supply-voltage rejection	n ratio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V _O = 1.4 V	0°C	60	97		dB
	$(\Delta V_{DD}/\Delta V_{IO})$			•	70°C	60	98		
					25°C		29	46	
I _{DD}	Supply current (two am	plifiers)	V _O = 5 V, No load	$V_{IC} = 5 V$	0°C		36	66	μΑ
			INO IOAU		70°C		22	40	

[†] Full range is 0°C to 70°C.

NOTES: 4 The typical values of input bias current and input offset current below 5 pA were determined mathematically.



⁵ This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †	TL:	C27L2I C27L2A C27L2B C27L7I		UNIT
						MIN	TYP	MAX	
		TLC27L2I	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	
		TLC2/L2I	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			13	mV
		TI COZI OAI	V _O = 1.4 V,	$V_{IC} = 0$,	25°C		0.9	5	IIIV
\/	Input offset voltage	TLC27L2AI	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			7	
VIO	input onset voltage	TLC27L2BI	$V_0 = 1.4 V,$	$V_{IC} = 0$,	25°C		240	2000	
		TLC2/L2BI	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			3500	/
		TI C071 71	$V_0 = 1.4 V,$	$V_{IC} = 0$,	25°C		170	500	μV
		TLC27L7I	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			2000	
αΝΙΟ	Average temperature co input offset voltage	efficient of			25°C to 85°C		1.1		μV/°C
		N. a	V 05V	.,	25°C		0.1	60	
lιο	Input offset current (see	Note 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	85°C		24	1000	рA
				.,	25°C		0.6	60	
I _{IB}	Input bias current (see I	Note 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	85°C		200	2000	рA
	Common-mode input vo	ltage range			25°C	-0.2 to 4	-0.3 to 4.2		V
VICR	(see Note 5)	go rango			Full range	-0.2 to 3.5			V
					25°C	3.2	4.1		
∨он	High-level output voltag	е	V _{ID} = 100 mV,	$R_L = 1 M\Omega$	-40°C	3	4.1		V
					85°C	3	4.2		
					25°C		0	50	
VOL	Low-level output voltage)	$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
				-	85°C		0	50	
					25°C	50	480		
AVD	Large-signal differential voltage amplification		$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 1 M\Omega$	-40°C	50	900		V/mV
	voltage amplification				85°C	50	330		
					25°C	65	94		
CMRR	Common-mode rejection	n ratio	$V_{IC} = V_{ICR}min$		-40°C	60	95		dB
					85°C	60	95		
					25°C	70	97		
ksvr	Supply-voltage rejection (ΔV _{DD} /ΔV _{IO})	ratio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V _O = 1.4 V	-40°C	60	97		dB
	ישיישטיים (טויים יישי				85°C	60	98		
		-	.,	.,	25°C		20	34	
I_{DD}	Supply current (two amp	olifiers)	$V_O = 2.5 \text{ V},$ No load	$V_{IC} = 2.5 V$,	-40°C		31	54	μΑ
			1.0.1000		85°C		15	26	

[†]Full range is -40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



^{5.} This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, $V_{\mbox{DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	T _A †	TL TL	C27L2I C27L2A C27L2B C27L7I		UNIT
						MIN	TYP	MAX	
		TLC27L2I	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		1.1	10	
		12027221	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			13	mV
		TLC27L2AI	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		0.9	5	111.
VIO	Input offset voltage	1202722711	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			7	
100	input onset voltage	TLC27L2BI	$V_{O} = 1.4 V$,	$V_{IC} = 0$,	25°C		235	2000	
		TEGZTEZBI	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			3500	μV
		TLC27L7I	$V_0 = 1.4 V$,	$V_{IC} = 0$,	25°C		190	800	μν
		TLCZ/L/T	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			2900	
αΛΙΟ	Average temperature co offset voltage	efficient of input			25°C to 85°C		1		μV/°C
			., -,,		25°C		0.1	60	
IIO	Input offset current (see	Note 4)	$V_0 = 5 V$,	$V_{IC} = 5 V$	85°C		26	1000	рA
					25°C		0.7	60	_
IB	Input bias current (see N	lote 4)	$V_0 = 5 V$,	$V_{IC} = 5 V$	85°C		220	2000	рA
	Common-mode input vo	Itage range			25°C	-0.2 to 9	-0.3 to 9.2		V
VICR	(see Note 5)	0 0			Full range	-0.2 to 8.5			V
					25°C	8	8.9		
∨он	High-level output voltage)	V _{ID} = 100 mV,	$R_L = 1 M\Omega$	-40°C	7.8	8.9		V
					85°C	7.8	8.9		
					25°C		0	50	
VOL	Low-level output voltage		$V_{1D} = -100 \text{ mV},$	$I_{OL} = 0$	-40°C		0	50	mV
					85°C		0	50	
					25°C	50	860		
AVD	Large-signal differential amplification	voltage	$V_{O} = 1 \text{ V to 6 V},$	$R_L = 1 M\Omega$	-40°C	50	1550		V/mV
	amplification			_	85°C	50	585		
					25°C	65	97		
CMRR	Common-mode rejection	ratio	V _{IC} = V _{ICR} min		-40°C	60	97		dB
	·				85°C	60	98		
					25°C	70	97		
ksvr	Supply-voltage rejection	ratio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	V _O = 1.4 V	-40°C	60	97		dB
	(ΔV _{DD} /ΔV _{IO})		,	•	85°C	60	98		
					25°C		29	46	
IDD	Supply current (two amp	lifiers)	$V_O = 5 V$	$V_{IC} = 5 V$	-40°C		49	86	μΑ
			No load		85°C		20	36	

[†]Full range is -40°C to 85°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.



^{5.} This range also applies to each input individually.

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electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

	PARAMETER		TEST CONI	DITIONS	T _A †		.C27L2N .C27L7N		UNIT
						MIN	TYP	MAX	
		TI COZI OM	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	\/
V	lanut affaat valtaas	TLC27L2M	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			12	mV
VIO	Input offset voltage	TI 0071 714	V _O = 1.4 V,	V _{IC} = 0,	25°C		170	500	
ı		TLC27L7M	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			3750	μV
αΛΙΟ	Average temperature of input offset voltage	coefficient of			25°C to 125°C		1.4		μV/°C
		- NI-1- 4\	V 0.5.V		25°C		0.1	60	pА
ΙΟ	Input offset current (se	e Note 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	125°C		1.4	15	nA
	Lancet Blancommunit (acco	NI-1- AV	V 05V	.,	25°C		0.6	60	pА
I _{IB}	Input bias current (see	Note 4)	$V_0 = 2.5 V$,	$V_{IC} = 2.5 V$	125°C		9	35	nA
VICR	Common-mode input v	roltage range			25°C	0 to 4	-0.3 to 4.2		V
VICR	(see Note 5)				Full range	0 to 3.5			>
					25°C	3.2	4.1		
Vон	High-level output voltage	ge	$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	−55°C	3	4.1		V
					125°C	3	4.2		
					25°C		0	50	
VOL	Low-level output voltag	je	$V_{ID} = -100 \text{ mV},$	IOL = 0	−55°C		0	50	mV
					125°C		0	50	
	Large-signal differentia	l voltogo			25°C	50	500		
AVD	amplification	ii voitage	$V_0 = 0.25 \text{ V to 2 V},$	$R_L = 1 M\Omega$	−55°C	25	1000		V/mV
	ap				125°C	25	200		
					25°C	65	94		
CMRR	Common-mode rejection	on ratio	$V_{IC} = V_{ICR}min$		−55°C	60	95		dB
					125°C	60	85		
	Supply-voltage rejection	en ratio			25°C	70	97		
k _{SVR}	(ΔVDD/ΔVIO)	יוו ומנוט	$V_{DD} = 5 V \text{ to } 10 V,$	$V_0 = 1.4 \text{ V}$	−55°C	60	97		dB
	(- : ''' - '' - '' - '''				125°C	60	98		
			Vo - 2.5.V	\/\.o = 2.5.\/	25°C		20	34	
I_{DD}	Supply current (two an	nplifiers)	V _O = 2.5 V, No load	$V_{IC} = 2.5 V,$	−55°C		35	60	μΑ
					125°C		14	24	

 $^{^{\}dagger}$ Full range is -55°C to 125 $^{\circ}\text{C}.$

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.



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electrical characteristics at specified free-air temperature, $V_{\mbox{DD}}$ = 10 V (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS	T _A †		.C27L2N .C27L7N		UNIT
						MIN	TYP	MAX	
		TI C071 0M	V _O = 1.4 V,	V _{IC} = 0,	25°C		1.1	10	\/
\/	lanut offeet voltege	TLC27L2M	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			12	mV
VIO	Input offset voltage	TLC27L7M	VO = 1.4 V,	V _{IC} = 0,	25°C		190	800	\/
		I LC2/L/M	$R_S = 50 \Omega$,	$R_L = 1 M\Omega$	Full range			4300	μV
αΛΙΟ	Average temperature co input offset voltage	efficient of			25°C to 125°C		1.4		μV/°C
		NI-1- 4	V 5.V		25°C		0.1	60	pА
lio	Input offset current (see	Note 4)	$V_0 = 5 V$,	$V_{IC} = 5 V$	125°C		1.8	15	nA
	lanut bing gumant (ann b	lata 4)	V 5.V	V 5V	25°C		0.7	60	pА
IB	Input bias current (see N	Note 4)	$V_{O} = 5 V,$	ΛIC = 2 Λ	125°C		10	35	nA
VICR	Common-mode input vo	Itage range			25°C	0 to 9	-0.3 to 9.2		V
VICR	(see Note 5)				Full range	0 to 8.5			٧
					25°C	8	8.9		
Vон	High-level output voltage	е	$V_{ID} = 100 \text{ mV},$	$R_L = 1 M\Omega$	−55°C	7.8	8.8		V
					125°C	7.8	9		
					25°C		0	50	
VOL	Low-level output voltage	•	$V_{ID} = -100 \text{ mV},$	$I_{OL} = 0$	−55°C		0	50	mV
					125°C		0	50	
	Lanca d'anal d'Mana Cal	11			25°C	50	860		
AVD	Large-signal differential amplification	voitage	$V_0 = 1 \text{ V to 6 V},$	$R_L = 1 M\Omega$	−55°C	25	1750		V/mV
	amplification				125°C	25	380		
					25°C	65	97		
CMRR	Common-mode rejection	n ratio	V _{IC} = V _{ICR} min		−55°C	60	97		dB
					125°C	60	91		
	Supply-voltage rejection	rotio			25°C	70	97		
ksvr	(ΔVDD/ΔVIO)	าสแบ	$V_{DD} = 5 \text{ V to } 10 \text{ V},$	$V_0 = 1.4 \text{ V}$	−55°C	60	97		dB
	(= · UU / = · IU /				125°C	60	98		
			V _O = 5 V,	V _{IC} = 5 V,	25°C		29	46	
IDD	Supply current (two amp	olifiers)	VO = 5 v,	AIC = 2A	−55°C		56	96	μΑ
					125°C		18	30	

[†]Full range is -55 °C to 125°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

5. This range also applies to each input individually.



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operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CO	NDITIONS	ТД	TL TL	C27L2C C27L2A C27L2E C27L7C	C SC	UNIT
					MIN	TYP	MAX	
				25°C		0.03		
			V _{I(PP)} = 1 V	0°C		0.04		
	Class rate at switz main	$R_L = 1 M\Omega$,	, ,	70°C		0.03		N//a
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.03		V/μs
		l	V _{I(PP)} = 2.5 V	0°C		0.03		
			, ,	70°C		0.02		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		68		nV/√ Hz
			_	25°C		5		
Вом	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 1 M\Omega$,	C _L = 20 pF, See Figure 1	0°C		6		kHz
		17[- 1 17152,	See rigule i	70°C		4.5		
			_	25°C		85		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF,$	0°C		100		kHz
		See Figure 3		70°C		65		
				25°C		34°		
φm	Phase margin	$V_{\parallel} = 10 \text{ mV},$ $C_{\parallel} = 20 \text{ pF},$	f = B ₁ , See Figure 3	0°C		36°		
		OL = 20 pr ,	occ rigule 3	70°C		30°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER	TEST CO	ONDITIONS	TA	TLC27L2C TLC27L2AC TLC27L2BC TLC27L7C			UNIT
					MIN	TYP	MAX	
				25°C		0.05		
			V _{I(PP)} = 1 V	0°C		0.05		
0.0	Olevanska skanika naja	$R_L = 1 M\Omega$,		70°C		0.04		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.04		V/μs
		Jan	V _{I(PP)} = 5.5 V	0°C		0.05		1
			1(0.17)	70°C		0.04		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		68		nV/√ Hz
				25°C		1		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$, $R_L = 1 M\Omega$,	$C_L = 20 pF$, See Figure 1	0°C		1.3		kHz
		1 1 10152,	See rigure r	70°C		0.9		1
			_	25°C		110		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	0°C		125		kHz
		See Figure 3		70°C		90		1
				25°C		38°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$	f = B ₁ ,	0°C		40°		1
		$C_L = 20 pF$,	See Figure 3	70°C		34°		1



operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CO	NDITIONS	ТД	TLC27L2I TLC27L2AI TLC27L2BI TLC27L7I			UNIT	
					MIN	TYP	MAX		
				25°C	0.03				
			V _{I(PP)} = 1 V	−40°C		0.04			
CD.	Claus note at social	$R_L = 1 M\Omega$,	, ,	85°C		0.03] ,,,	
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.03		V/μs	
			V _{I(PP)} = 2.5 V		0.04				
			, ,	85°C		0.02			
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		68		nV/√ Hz	
		$V_O = V_{OH},$ $R_L = 1 \text{ M}\Omega,$		25°C		5		nV/√ Hz kHz	
ВОМ	Maximum output-swing bandwidth		C _L = 20 pF, See Figure 1	-40°C		7			
			occ rigure r	85°C		4			
				25°C		85			
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF,$	-40°C		130		kHz	
		See rigule 3		85°C		55			
				25°C		34°			
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	-40°C		38°			
		ο <u> </u>		85°C		29°			

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER	TEST CO	NDITIONS	ТА	TLC27L2I TLC27L2AI TLC27L2BI TLC27L7I MIN TYP MAX			UNIT	
				25°C	IVIIIV	0.05	WAA		
			V _{I(PP)} = 1 V	-40°C		0.06			
		$R_L = 1 M\Omega$,	(FF)	85°C		0.03		1	
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.04		V/μs	
		See i iguie i	V _{I(PP)} = 5.5 V	-40°C		0.05			
			.(/	85°C		0.03			
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		68		nV/√ Hz	
		$V_O = V_{OH}$, $R_I = 1 M\Omega$,		25°C		1			
Вом	Maximum output-swing bandwidth		C _L = 20 pF, See Figure 1	-40°C		1.4		kHz	
		1 1 10152,	See rigure r	85°C		0.8			
		.,,		25°C		110			
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF$,	-40°C		155		kHz	
		ecc i iguio o		85°C		80			
		101/	, D	25°C		38°			
φm	Phase margin	$V_{\parallel} = 10 \text{ mV},$ $C_{\parallel} = 20 \text{ pF},$	f = B ₁ , See Figure 3	−40°C		42°			
				85°C		32°			

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operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CO	NDITIONS	TA	TLC27L2M TLC27L7M			UNIT
					MIN	TYP	MAX	
				25°C		0.03		
			V _{I(PP)} = 1 V	−55°C		0.04		
	Oleverate at with mate	$R_L = 1 M\Omega$,	. ,	125°C		0.02] ,,, ,
SR	Slew rate at unity gain	C _L = 20 pF, See Figure 1		25°C	0.03		V/μs	
		l coo r igaro r	V _{I(PP)} = 2.5 V	−55°C		0.04		
			, ,	125°C		0.02		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		68		nV/√ Hz
		$V_O = V_{OH},$ $R_L = 1 M\Omega,$	C _L = 20 pF, See Figure 1	25°C		5		kHz
Вом	Maximum output-swing bandwidth			−55°C		8		
				125°C		3		
				25°C		85		
В1	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF,$	−55°C		140		kHz
		See Figure 3		125°C		45		
				25°C		34°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	$f = B_1$, See Figure 3 $-55^{\circ}C$ 39°					
		ο_ – 20 ρι ,	oce rigule 3	125°C		25°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER Slew rate at unity gain	TEST CO	NDITIONS	TA	TLC27L2M TLC27L7M			UNIT
					MIN	TYP	MAX	
				25°C	0.05			
			V _{I(PP)} = 1 V	−55°C		0.06		
	Oleverate at with main	$R_L = 1 M\Omega$,		125°C		0.03		.,, .
SR	Siew rate at unity gain	C _L = 20 pF, See Figure 1		25°C		0.04		V/μs
		Ode rigule r	V _{I(PP)} = 5.5 V	−55°C		0.06		
			` ′	125°C		0.03		
Vn	Equivalent input noise voltage	f = 1 kHz, See Figure 2	$R_S = 20 \Omega$,	25°C		68		nV/√ Hz
		$V_O = V_{OH},$ $R_L = 1 \text{ M}\Omega,$	C _L = 20 pF, See Figure 1	25°C		1		kHz
Вом	Maximum output-swing bandwidth			−55°C		1.5		
				125°C		0.7		
				25°C		110		
B ₁	Unity-gain bandwidth	V _I = 10 mV, See Figure 3	$C_L = 20 pF,$	−55°C		165		kHz
		See Figure 3		125°C		70		
				25°C		38°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$ $C_{L} = 20 \text{ pF},$	f = B ₁ , See Figure 3	−55°C		43°		1
		OL = 20 μr,	See Figure 3	125°C		29°		

PARAMETER MEASUREMENT INFORMATION

single-supply versus split-supply test circuits

Because the TLC27L2 and TLC27L7 are optimized for single-supply operation, circuit configurations used for the various tests often present some inconvenience since the input signal, in many cases, must be offset from ground. This inconvenience can be avoided by testing the device with split supplies and the output load tied to the negative rail. A comparison of single-supply versus split-supply test circuits is shown in Figure 1. The use of either circuit gives the same result.

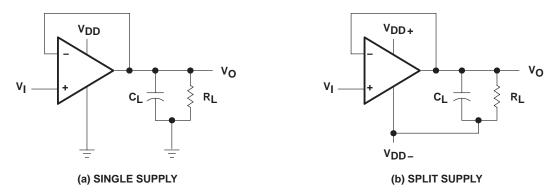


Figure 1. Unity-Gain Amplifier

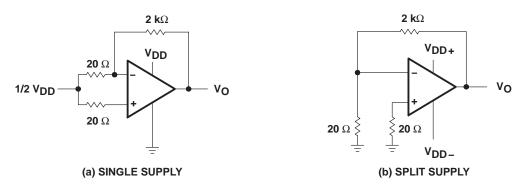


Figure 2. Noise-Test Circuit

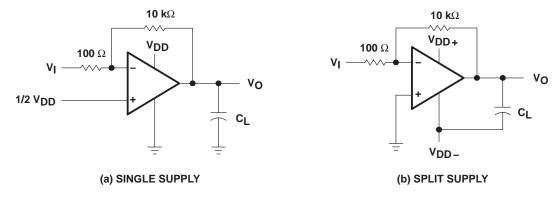


Figure 3. Gain-of-100 Inverting Amplifier

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PARAMETER MEASUREMENT INFORMATION

input bias current

Because of the high input impedance of the TLC27L2 and TLC27L7 operational amplifiers, attempts to measure the input bias current can result in erroneous readings. The bias current at normal room ambient temperature is typically less than 1 pA, a value that is easily exceeded by leakages on the test socket. Two suggestions are offered to avoid erroneous measurements:

- 1. Isolate the device from other potential leakage sources. Use a grounded shield around and between the device inputs (see Figure 4). Leakages that would otherwise flow to the inputs are shunted away.
- Compensate for the leakage of the test socket by actually performing an input bias current test (using a picoammeter) with no device in the test socket. The actual input bias current can then be calculated by subtracting the open-socket leakage readings from the readings obtained with a device in the test socket.

One word of caution: many automatic testers as well as some bench-top operational amplifier testers use the servo-loop technique with a resistor in series with the device input to measure the input bias current (the voltage drop across the series resistor is measured and the bias current is calculated). This method requires that a device be inserted into the test socket to obtain a correct reading; therefore, an open-socket reading is not feasible using this method.

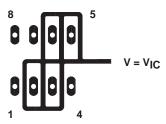


Figure 4. Isolation Metal Around Device Inputs (JG and P packages)

low-level output voltage

To obtain low-supply-voltage operation, some compromise was necessary in the input stage. This compromise results in the device low-level output being dependent on both the common-mode input voltage level as well as the differential input voltage level. When attempting to correlate low-level output readings with those quoted in the electrical specifications, these two conditions should be observed. If conditions other than these are to be used, please refer to Figure 14 through Figure 19 in the Typical Characteristics of this data sheet.

input offset voltage temperature coefficient

Erroneous readings often result from attempts to measure temperature coefficient of input offset voltage. This parameter is actually a calculation using input offset voltage measurements obtained at two different temperatures. When one (or both) of the temperatures is below freezing, moisture can collect on both the device and the test socket. This moisture results in leakage and contact resistance, which can cause erroneous input offset voltage readings. The isolation techniques previously mentioned have no effect on the leakage since the moisture also covers the isolation metal itself, thereby rendering it useless. It is suggested that these measurements be performed at temperatures above freezing to minimize error.



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PARAMETER MEASUREMENT INFORMATION

full-power response

Full-power response, the frequency above which the operational amplifier slew rate limits the output voltage swing, is often specified two ways: full-linear response and full-peak response. The full-linear response is generally measured by monitoring the distortion level of the output while increasing the frequency of a sinusoidal input signal until the maximum frequency is found above which the output contains significant distortion. The full-peak response is defined as the maximum output frequency, without regard to distortion, above which full peak-to-peak output swing cannot be maintained.

Because there is no industry-wide accepted value for significant distortion, the full-peak response is specified in this data sheet and is measured using the circuit of Figure 1. The initial setup involves the use of a sinusoidal input to determine the maximum peak-to-peak output of the device (the amplitude of the sinusoidal wave is increased until clipping occurs). The sinusoidal wave is then replaced with a square wave of the same amplitude. The frequency is then increased until the maximum peak-to-peak output can no longer be maintained (see Figure 5). A square wave is used to allow a more accurate determination of the point at which the maximum peak-to-peak output is reached.

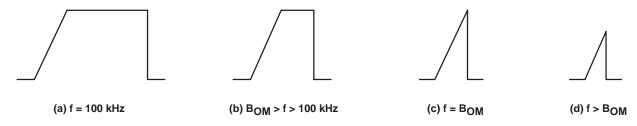


Figure 5. Full-Power-Response Output Signal

test time

Inadequate test time is a frequent problem, especially when testing CMOS high-volume, short-test-time environment. Internal capacitances are inherently higher in CMOS devices and require longer test times than their bipolar and BiFET counterparts. The problem becomes more pronounced with reduced supply levels and lower temperatures.

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TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
VIO	Input offset voltage	Distribution	6, 7
ανιο	Temperature coefficient of input offset voltage	Distribution	8, 9
VOH	High-level output voltage	vs High-level output current vs Supply voltage vs Free-air temperature	10, 11 12 13
V _{OL}	Low-level output voltage	vs Differential input voltage vs Free-air temperature vs Low-level output current	14,16 15,17 18, 19
AVD	Large-signal differential voltage amplification	vs Supply voltage vs Free-air temperature vs Frequency	20 21 32, 33
I _{IB}	Input bias current	vs Free-air temperature	22
lιο	Input offset current	vs Free-air temperature	22
V _{IC}	Common-mode input voltage	vs Supply voltage	23
l _{DD}	Supply current	vs Supply voltage vs Free-air temperature	24 25
SR	Slew rate	vs Supply voltage vs Free-air temperature	26 27
	Normalized slew rate	vs Free-air temperature	28
V _{O(PP)}	Maximum peak-to-peak output voltage	vs Frequency	29
В ₁	Unity-gain bandwidth	vs Free-air temperature vs Supply voltage	30 31
φm	Phase margin	vs Supply voltage vs Free-air temperature vs Capacitive Load	34 35 36
Vn	Equivalent input noise voltage	vs Frequency	37
	Phase shift	vs Frequency	32, 33



TYPICAL CHARACTERISTICS

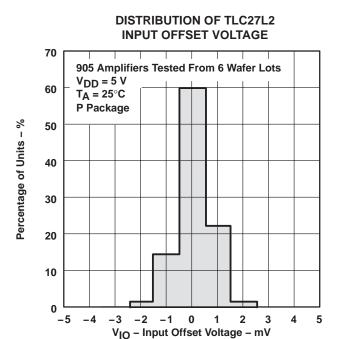
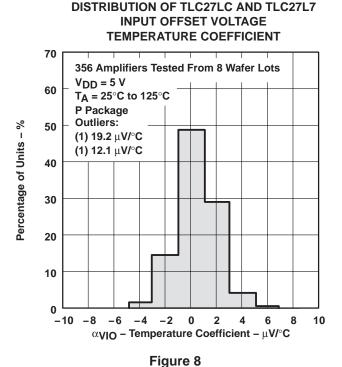


Figure 6



DISTRIBUTION OF TLC27L2 INPUT OFFSET VOLTAGE

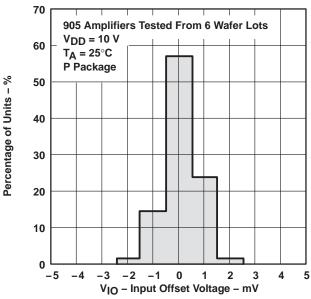


Figure 7

DISTRIBUTION OF TLC27LC AND TLC27L7 INPUT OFFSET VOLTAGE TEMPERATURE COEFFICIENT

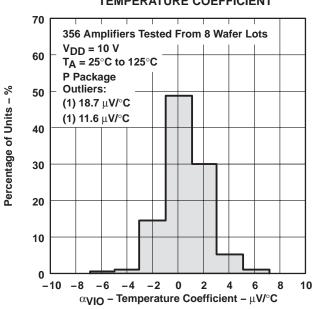


Figure 9

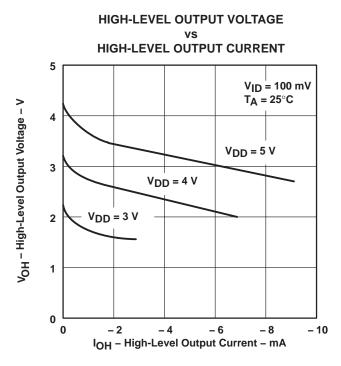
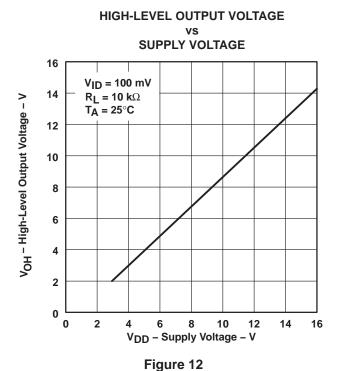


Figure 10



HIGH-LEVEL OUTPUT VOLTAGE **HIGH-LEVEL OUTPUT CURRENT**

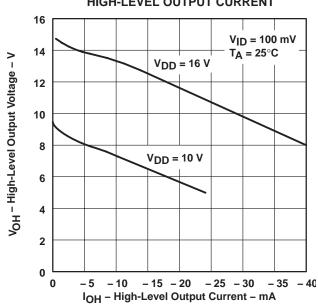


Figure 11

HIGH-LEVEL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE

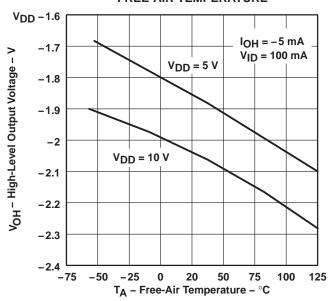


Figure 13

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



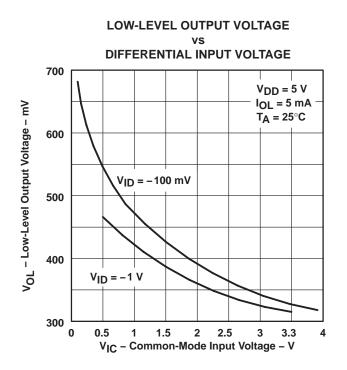


Figure 14

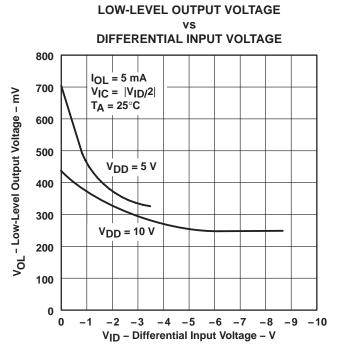


Figure 16

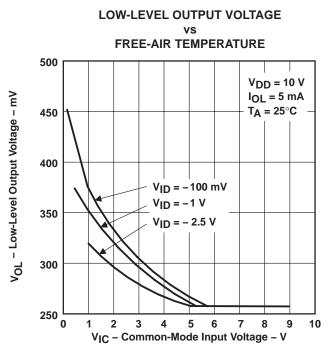


Figure 15

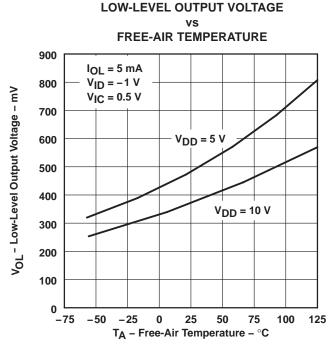
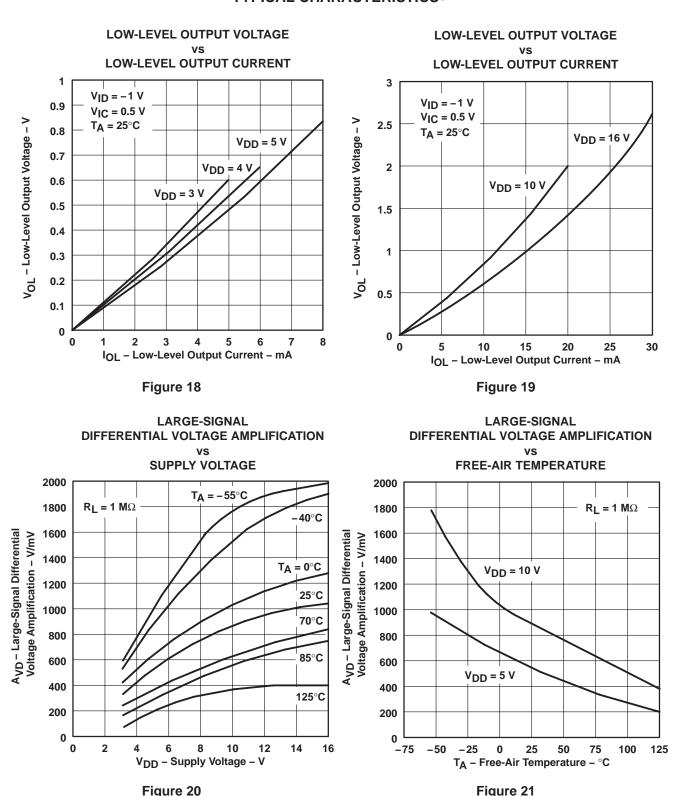


Figure 17

[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.





[†]Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

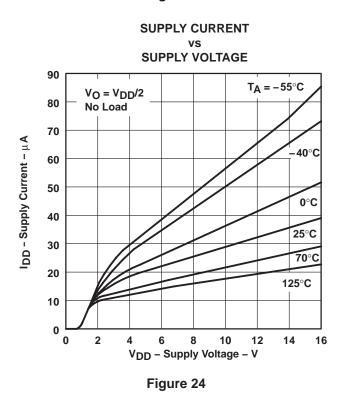


INPUT BIAS CURRENT AND INPUT OFFSET CURRENT

FREE-AIR TEMPERATURE 10000 IB and I_{IO} - Input Bias and Offset Currents - pA $V_{DD} = 10 V$ V_{IC} = 5 V See Note A 1000 lιΒ 100 lιο 10 1 0.1 25 65 85 105 125 - Free-Air Temperature - °C

NOTE A: The typical values of input bias current and input offset current below 5 pA were determined mathematically.

Figure 22



COMMON-MODE INPUT VOLTAGE POSITIVE LIMIT

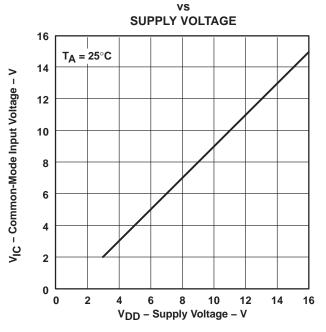
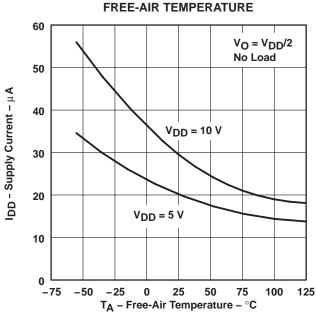


Figure 23

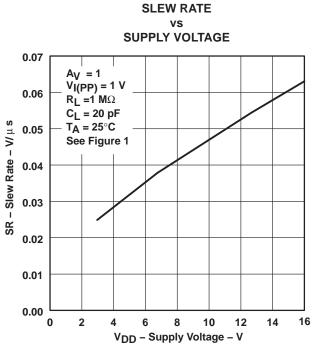
SUPPLY CURRENT vs



† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

Figure 25





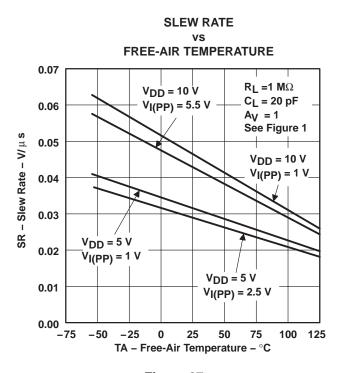
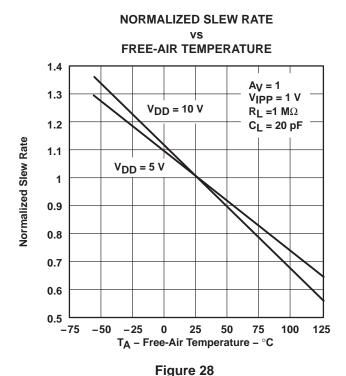
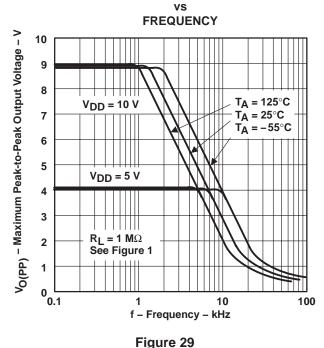


Figure 26

Figure 27

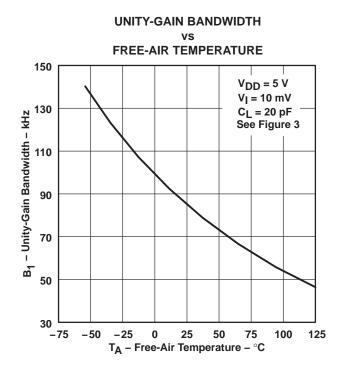


MAXIMUM-PEAK-TO-PEAK OUTPUT VOLTAGE



†Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.





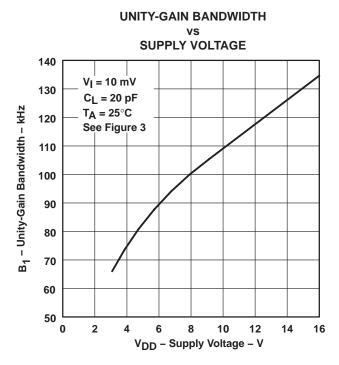


Figure 30

Figure 31

LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

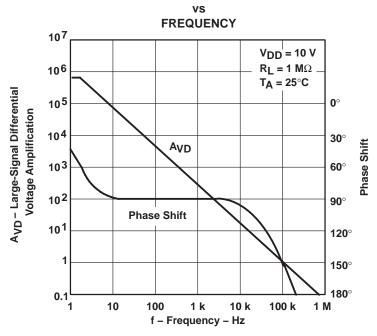


Figure 32

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



LARGE-SIGNAL DIFFERENTIAL VOLTAGE **AMPLIFICATION AND PHASE SHIFT**

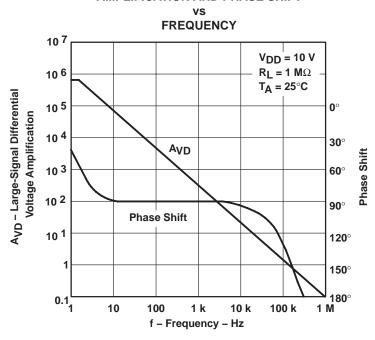
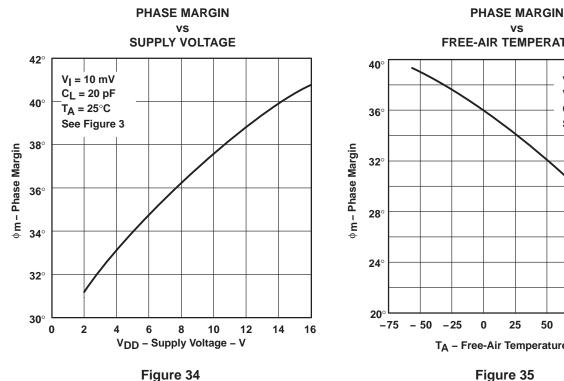


Figure 33



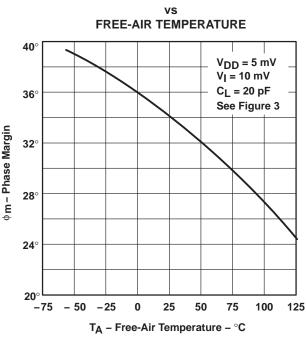
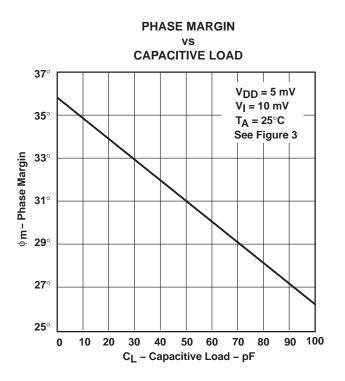


Figure 35

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS





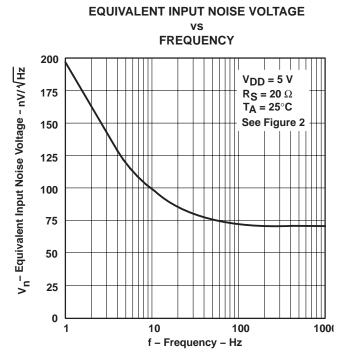


Figure 37

single-supply operation

While the TLC27L2 and TLC27L7 perform well using dual power supplies (also called balanced or split supplies), the design is optimized for single-supply operation. This design includes an input common-mode voltage range that encompasses ground as well as an output voltage range that pulls down to ground. The supply voltage range extends down to 3 V (C-suffix types), thus allowing operation with supply levels commonly available for TTL and HCMOS; however, for maximum dynamic range, 16-V single-supply operation is recommended.

Many single-supply applications require that a voltage be applied to one input to establish a reference level that is above ground. A resistive voltage divider is usually sufficient to establish this reference level (see Figure 38). The low input bias current of the TLC27L2 and TLC27L7 permits the use of very large resistive values to implement the voltage divider, thus minimizing power consumption.

The TLC27L2 and TLC27L7 work well in conjunction with digital logic; however, when powering both linear devices and digital logic from the same power supply, the following precautions are recommended:

- Power the linear devices from separate bypassed supply lines (see Figure 39); otherwise, the linear device supply rails can fluctuate due to voltage drops caused by high switching currents in the digital logic.
- 2. Use proper bypass techniques to reduce the probability of noise-induced errors. Single capacitive decoupling is often adequate; however, high-frequency applications may require RC decoupling.

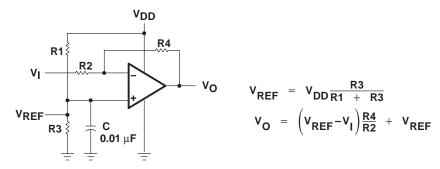


Figure 38. Inverting Amplifier With Voltage Reference

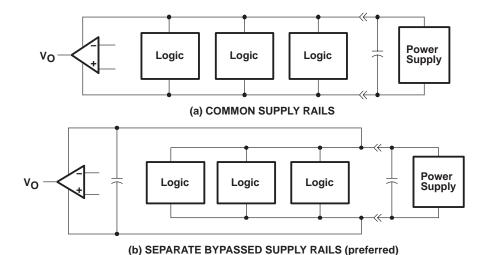


Figure 39. Common Versus Separate Supply Rails



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APPLICATION INFORMATION

input characteristics

The TLC27L2 and TLC27L7 are specified with a minimum and a maximum input voltage that, if exceeded at either input, could cause the device to malfunction. Exceeding this specified range is a common problem, especially in single-supply operation. Note that the lower range limit includes the negative rail, while the upper range limit is specified at V_{DD} –1 V at T_A = 25°C and at V_{DD} –1.5 V at all other temperatures.

The use of the polysilicon-gate process and the careful input circuit design gives the TLC27L2 and TLC27L7 very good input offset voltage drift characteristics relative to conventional metal-gate processes. Offset voltage drift in CMOS devices is highly influenced by threshold voltage shifts caused by polarization of the phosphorus dopant implanted in the oxide. Placing the phosphorus dopant in a conductor (such as a polysilicon gate) alleviates the polarization problem, thus reducing threshold voltage shifts by more than an order of magnitude. The offset voltage drift with time has been calculated to be typically 0.1 μ V/month, including the first month of operation.

Because of the extremely high input impedance and resulting low bias current requirements, the TLC27L2 and TLC27L7 are well suited for low-level signal processing; however, leakage currents on printed circuit boards and sockets can easily exceed bias current requirements and cause a degradation in device performance. It is good practice to include guard rings around inputs (similar to those of Figure 4 in the *Parameter Measurement Information* section). These guards should be driven from a low-impedance source at the same voltage level as the common-mode input (see Figure 40).

Unused amplifiers should be connected as grounded unity-gain followers to avoid possible oscillation.

noise performance

The noise specifications in operational amplifier circuits are greatly dependent on the current in the first-stage differential amplifier. The low input bias current requirements of the TLC27L2 and TLC27L7 result in a low noise current, which is insignificant in most applications. This feature makes the devices especially favorable over bipolar devices when using values of circuit impedance greater than $50~\mathrm{k}\Omega$, since bipolar devices exhibit greater noise currents.

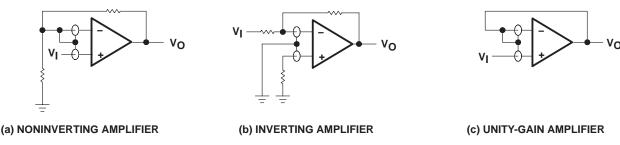


Figure 40. Guard-Ring Schemes

output characteristics

The output stage of the TLC27L2 and TLC27L7 is designed to sink and source relatively high amounts of current (see typical characteristics). If the output is subjected to a short-circuit condition, this high current capability can cause device damage under certain conditions. Output current capability increases with supply voltage.

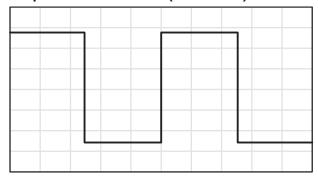
All operating characteristics of the TLC27L2 and TLC27L7 were measured using a 20-pF load. The devices drive higher capacitive loads; however, as output load capacitance increases, the resulting response pole occurs at lower frequencies, thereby causing ringing, peaking, or even oscillation (see Figure 41). In many cases, adding a small amount of resistance in series with the load capacitance alleviates the problem.



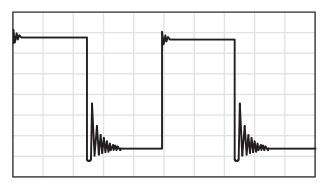
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APPLICATION INFORMATION

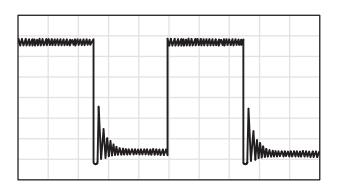
output characteristics (continued)



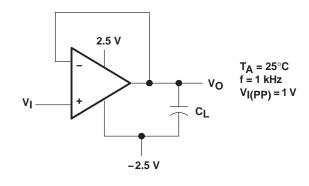
(a) $C_L = 20 pF$, $R_L = NO LOAD$



(b) $C_L = 260 pF$, $R_L = NO LOAD$



(c) $C_L = 310 \text{ pF}, R_L = NO \text{ LOAD}$

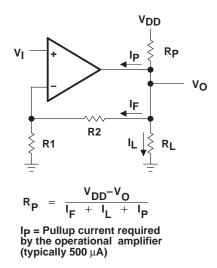


(d) TEST CIRCUIT

Figure 41. Effect of Capacitive Loads and Test Circuit

Although the TLC27L2 and TLC27L7 possess excellent high-level output voltage and current capability, methods for boosting this capability are available, if needed. The simplest method involves the use of a pullup resistor (R_P) connected from the output to the positive supply rail (see Figure 42). There are two disadvantages to the use of this circuit. First, the NMOS pulldown transistor N4 (see equivalent schematic) must sink a comparatively large amount of current. In this circuit, N4 behaves like a linear resistor with an on-resistance between approximately $60~\Omega$ and $180~\Omega$, depending on how hard the operational amplifier input is driven. With very low values of R_P, a voltage offset from 0 V at the output occurs. Second, pullup resistor R_P acts as a drain load to N4 and the gain of the operational amplifier is reduced at output voltage levels where N5 is not supplying the output current.

output characteristics (continued)



v_C

Figure 42. Resistive Pullup to Increase VOH

Figure 43. Compensation for Input Capacitance

feedback

Operational amplifier circuits nearly always employ feedback, and since feedback is the first prerequisite for oscillation, some caution is appropriate. Most oscillation problems result from driving capacitive loads (discussed previously) and ignoring stray input capacitance. A small-value capacitor connected in parallel with the feedback resistor is an effective remedy (see Figure 43). The value of this capacitor is optimized empirically.

electrostatic discharge protection

The TLC27L2 and TLC27L7 incorporate an internal electrostatic discharge (ESD) protection circuit that prevents functional failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.2. Care should be exercised, however, when handling these devices, as exposure to ESD may result in the degradation of the device parametric performance. The protection circuit also causes the input bias currents to be temperature dependent and have the characteristics of a reverse-biased diode.

latch-up

Because CMOS devices are susceptible to latch-up due to their inherent parasitic thyristors, the TLC27L2 and TLC27L7 inputs and outputs were designed to withstand -100-mA surge currents without sustaining latch-up; however, techniques should be used to reduce the chance of latch-up whenever possible. Internal protection diodes should not, by design, be forward biased. Applied input and output voltage should not exceed the supply voltage by more than 300 mV. Care should be exercised when using capacitive coupling on pulse generators. Supply transients should be shunted by the use of decoupling capacitors (0.1 μ F typical) located across the supply rails as close to the device as possible.

The current path established if latch-up occurs is usually between the positive supply rail and ground and can be triggered by surges on the supply lines and/or voltages on either the output or inputs that exceed the supply voltage. Once latch-up occurs, the current flow is limited only by the impedance of the power supply and the forward resistance of the parasitic thyristor and usually results in the destruction of the device. The chance of latch-up occurring increases with increasing temperature and supply voltages.

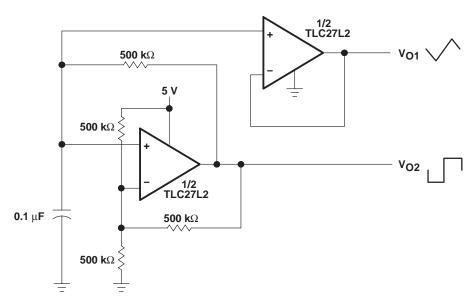
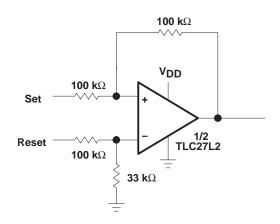


Figure 44. Multivibrator



NOTE: $V_{DD} = 5 \text{ V to } 16 \text{ V}$

Figure 45. Set/Reset Flip-Flop

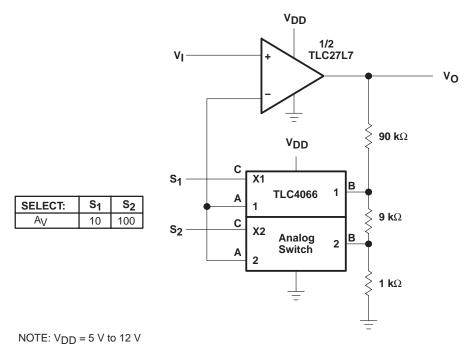
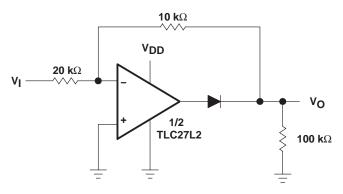
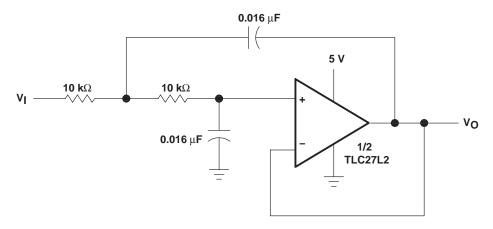


Figure 46. Amplifier With Digital Gain Selection



NOTE: $V_{DD} = 5 \text{ V}$ to 16 V

Figure 47. Full-Wave Rectifier



NOTE: Normalized to f_{C} = 1 kHz and R_{L} = 10 $k\Omega$

Figure 48. Two-Pole Low-Pass Butterworth Filter

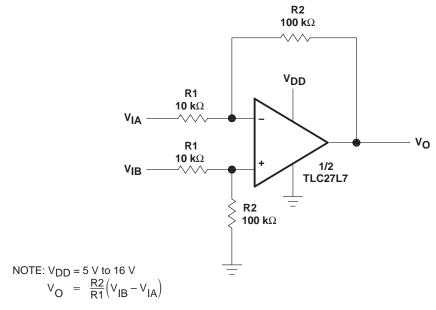


Figure 49. Difference Amplifier

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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
5962-89494032A	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	
5962-8949403PA	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	
5962-89494042A	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	
5962-8949404PA	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	
TLC27L2ACD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2ACDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2ACDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2ACDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2ACP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2ACPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2ACPSLE	OBSOLETE	so	PS	8		TBD	Call TI	Call TI	
TLC27L2AID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2AIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2AIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2AIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2AIP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2AIPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2AMFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	
TLC27L2AMJG	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	
TLC27L2AMJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	
TLC27L2BCD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2BCDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	



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Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TLC27L2BCDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2BCDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2BCP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2BCPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2BID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2BIDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2BIDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2BIDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2BIP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2BIPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2CPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2CPWG4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2CPWLE	OBSOLETE	TSSOP	PW	8		TBD	Call TI	Call TI	



23-May-2012

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TLC27L2CPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2CPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2IPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L2IPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2IPWG4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2IPWLE	OBSOLETE	TSSOP	PW	8		TBD	Call TI	Call TI	
TLC27L2IPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2IPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2MD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2MDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2MDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2MDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L2MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	
TLC27L2MJG	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	
TLC27L2MJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	<u> </u>





www.ti.com 23-May-2012

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TLC27L7CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7CP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L7CPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L7CPSR	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7CPSRG4	ACTIVE	SO	PS	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC27L7IP	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L7IPE4	ACTIVE	PDIP	Р	8	50	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC27L7MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI	
TLC27L7MJG	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	
TLC27L7MJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.



PACKAGE OPTION ADDENDUM

23-May-2012

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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OTHER QUALIFIED VERSIONS OF TLC27L2. TLC27L2M:

Catalog: TLC27L2

Military: TLC27L2M

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

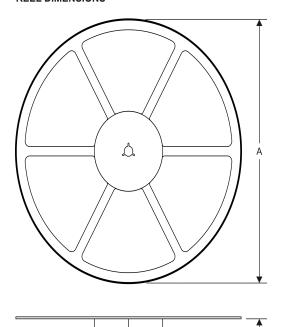
PACKAGE MATERIALS INFORMATION

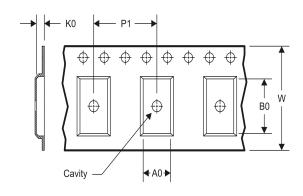
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TAPE DIMENSIONS

TAPE AND REEL INFORMATION

REEL DIMENSIONS





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC27L2ACDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27L2AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27L2BCDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27L2BIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27L2CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27L2CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TLC27L2CPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLC27L2IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27L2IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
TLC27L2MDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27L7CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLC27L7CPSR	SO	PS	8	2000	330.0	16.4	8.2	6.6	2.5	12.0	16.0	Q1
TLC27L7IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLC27L2ACDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27L2AIDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27L2BCDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27L2BIDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27L2CDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27L2CPSR	SO	PS	8	2000	367.0	367.0	38.0
TLC27L2CPWR	TSSOP	PW	8	2000	367.0	367.0	35.0
TLC27L2IDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27L2IPWR	TSSOP	PW	8	2000	367.0	367.0	35.0
TLC27L2MDR	SOIC	D	8	2500	367.0	367.0	35.0
TLC27L7CDR	SOIC	D	8	2500	340.5	338.1	20.6
TLC27L7CPSR	SO	PS	8	2000	367.0	367.0	38.0
TLC27L7IDR	SOIC	D	8	2500	340.5	338.1	20.6

JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8

FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004



P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE

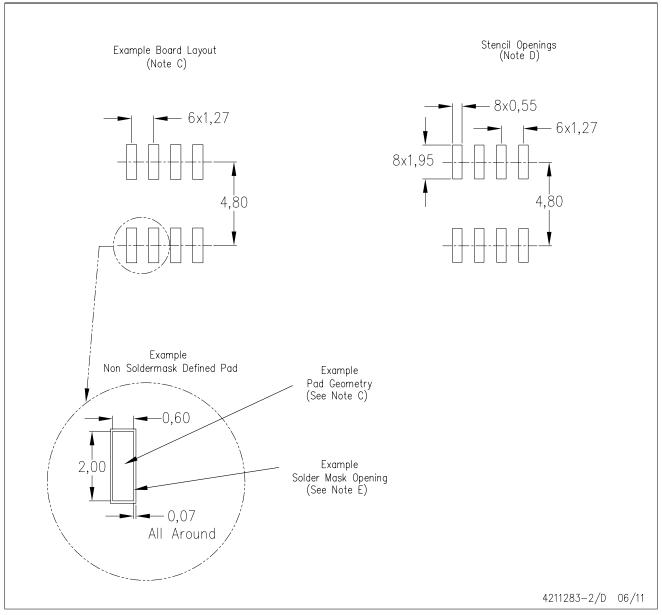


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



PS (R-PDSO-G8)

PLASTIC SMALL OUTLINE

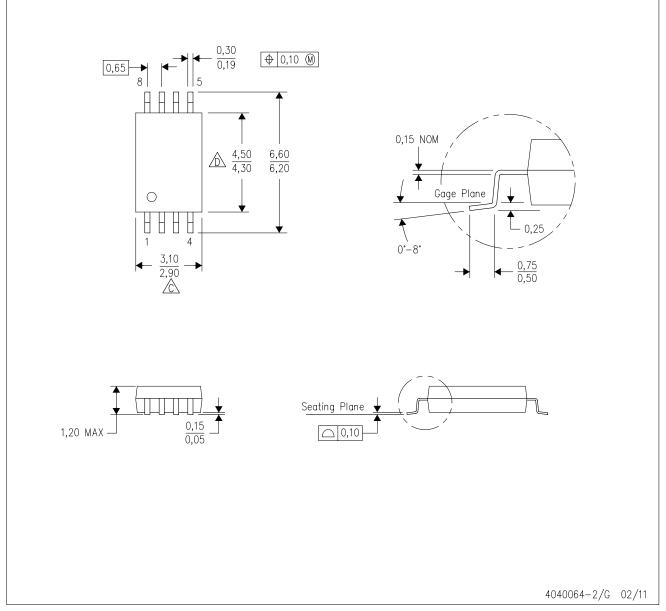


- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



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